PCN# : P647AA
Issue Date : Aug. 17, 2016

DESIGN/PROCESS CHANGE NOTIFICATION

This is to inform you that a change is being made to the products listed below.

Unless otherwise indicated in the details of this notification, the identified change will have no impact on product quality, reliability, electrical, visual or mechanical performance and affected products will remain fully compliant to all published specifications. Products incorporating this change may be shipped interchangeably with existing unchanged products.

This change is planned to take effect in 90 calendar days from the date of this notification. Please work with your local Fairchild Sales Representative to manage your inventory of unchanged product if your evaluation of this change will require more than 90 calendar days.

Please contact your local Customer Quality Engineer within 30 days of receipt of this notification if you require any additional data or samples.

Implementation of change:

Expected First Shipment Date for Changed Product :Nov. 15, 2016

Expected First Date Code of Changed Product :1647

Description of Change (From) :
Wafer fabrication at TowerJazz Israel

Description of Change (To) :
8-inch wafer fabrication at Fairchild in Bucheon, South Korea and wafer fabrication at TowerJazz Israel

Reason for Change:
Fairchild Semiconductor is increasing wafer fabrication capacity by qualifying 8-inch wafer fabrication line at Fairchild Semiconductor Bucheon Korea. Quality and reliability remain at the highest standards already demonstrated within Fairchild's existing products. The reliability qualification results used to qualify the 8-inch wafer fabrication line are summarized below.
Design, die size and layout of the affected products will remain unchanged. There are no changes in the datasheet or electrical performance.

Affected Product(s):

9V49_NB9V004	FDC6301N	FDC6303N
FDC6304P	FDC653N	FDG6301N
FDG6301N_G	FDG6303N	FDG6304P
FDG6321C	FDG6322C	FDG6323L
FDN337N	FDN357N	FDS8433A
FDS8433A_G	FDS8928A	FDV301N_G
FDV301N_NB9V003	FDV303N	FDV304P
FDV304P_D87Z	NDS331N	NDS332P
NDS355AN	NDS355AN_NB9L007A	NDS355N
NDT452AP		

Qualification Plan	Device	Package	Process	No. of Lots
Q20160056	FDC6303N	SSOT6	5.0M N	2

Test Description:	Condition:	Standard :	Duration:	Results:
MSL1 Precondition	260°C, 3 cycles	**JESD22-A113**		0/640
Highly Accelerated Stress Test	130°C, 85%RH, Vr = +20V	**JESD22-A110**	96 hrs	0/160
High Temperature Gate Bias	150°C, Vgs = +8V	**JESD22-A108**	1000hrs	15-Sep 2016
High Temperature Reverse Bias	150°C, Vr = +20V	**JESD22-A108**	1000hrs	0/160
Power Cycle	Delta 100CC, 2.0 Min cyc	**JESD22-A105**	10000 cycles	0/160
High Temperature Storage Life	150°C	**JESD22-A103**	1000hrs	0/160
Temperature Cycle	-65°C, 150°C	**JESD22-A104**	500 cycles	15-Sep-2016

Qualification Plan	Device	Package	Process	No. of Lots
Q20160056	FDS8433A	SO8-Single	10.0M P	3

Test Description:	Condition:	Standard :	Duration:	Results:
MSL1 Precondition	260°C, 3 cycles	**JESD22-A113**		0/720
Highly Accelerated Stress Test	130°C, 85%RH, Vr = -16V	**JESD22-A110**	96 hrs	0/240
High Temperature Gate Bias	150°C, Vgs = -8V	**JESD22-A108**	1000hrs	0/240
High Temperature Reverse Bias	150°C, Vr = - 16V	**JESD22-A108**	1000hrs	0/240
Power Cycle	Delta 100CC, 2.0 Min cyc	**JESD22-A105**	10000 cycles	0/240
Temperature Cycle	-65°C, 150°C	**JESD22-A104**	1000 cycles	0/240

Qualification Plan	Device	Package	Process	No. of Lots
Q20160056	NDB6030PL	TO-263	05.0 P	1

Test Description:	Condition:	Standard :	Duration:	Results:
MSL1 Precondition	260°C, 3 cycles	**JESD22-A113**		01-Aug 2016
Highly Accelerated Stress Test	130°C, 85%RH, Vr = +20V	**JESD22-A110**	96 hrs	09-Sep 2016
High Temperature Gate Bias	150°C, Vgs = +8V	**JESD22-A108**	1000hrs	27-Sep 2016
High Temperature Reverse Bias	150°C, Vr = +20V	**JESD22-A108**	1000hrs	27-Sep 2016
Power Cycle	Delta 100CC, 2.0 Min cyc	**JESD22-A105**	8572 cycles	30-Sep 2016
Temperature Cycle	-65°C, 150°C	**JESD22-A104**	500 cycles	22-Aug 2016